IRFM240 (JANTX2N7219)

PD-90555F

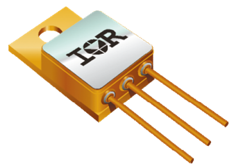
Power MOSFET
Thru-Hole (TO-254AA)
200V, 18A, N-channel, HEXFET™ MOSFET Technology

Features

- Simple drive requirements
- Hermetically sealed
- Electrically isolated
- Dynamic dv/dt rating
- Light-weight

Product Summary

- **Part number:** IRFM240 (JANTX2N7219), (JANTXV2N7219)
- **REF:** MIL-PRF-19500/596
- **$R_{DS(on),max}$:** 18 mΩ
- **I_D:** 18A



TO-254AA

Potential Applications

- DC-DC converter
- Motor drives

Product Validation

Qualified to JANTXV screening flow according to MIL-PRF-19500 for high-reliability applications

Description

IR HiRel HEXFET™ technology is advanced line of power MOSFET transistors. The efficient geometry design achieves very low on-state resistance combined with high transconductance. HEXFET™ transistors also feature all of the well-established advantages of MOSFETs, such as voltage control, fast switching and electrical parameter temperature stability. They are well-suited for applications such as switching power supplies, motor controls, inverters, high energy pulse circuits, and virtually any application where high reliability is required. The HEXFET™ transistor's totally isolated package eliminates the need for additional isolating material between the device and the heatsink. This improves thermal efficiency and reduces drain capacitance.

Ordering Information

Table 1 Ordering options

Part number	Package	Screening Level
IRFM240	TO-254AA	COTS
JANTX2N7219	TO-254AA	JANTX
JANTXV2N7219	TO-254AA	JANTXV

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1 Absolute Maximum Ratings

Table 2 Absolute Maximum Ratings (Pre-Irradiation)

Symbol	Parameter	Value	Unit
I_{D1} @ V_{GS} = 10V, T_C = 25°C	Continuous Drain Current	18	A
I_{D2} @ V_{GS} = 10V, T_C = 100°C	Continuous Drain Current	11	A
I_{DM} @ T_C = 25°C	Pulsed Drain Current [1]	72	A
P_D @ T_C = 25°C	Maximum Power Dissipation	125	W
	Linear Derating Factor	1.0	W/°C
V_{GS}	Gate-to-Source Voltage	± 20	V
E_{AS}	Single Pulse Avalanche Energy [2]	450	mJ
I_{AR}	Avalanche Current [1]	18	A
E_{AR}	Repetitive Avalanche Energy [1]	12.5	mJ
dv/dt	Peak Diode Reverse Recovery [3]	5.0	V/ns
T_J T_{STG}	Operating Junction and Storage Temperature Range	-55 to +150	°C
	Lead Temperature	300 (0.063 in. /1.6 mm from case for 10s)	
	Weight	9.3 (Typical)	g

[1] Repetitive Rating; Pulse width limited by maximum junction temperature.
[2] V_{DD} = 50V, starting T_J = 25°C, L = 1.3mH, Peak I_L = 18A, V_{GS} = 10V
[3] $I_{SD} \leq$ 18A, di/dt $\leq$ 150A/µs, $V_{DD} \leq$ 200V, $T_J \leq$ 150°C

2 Device Characteristics

2.1 Electrical Characteristics (Pre-Irradiation)

Table 3 Static and Dynamic Electrical Characteristics @ T_j = 25°C (Unless Otherwise Specified)

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions
BV_{DSS}	Drain-to-Source Breakdown Voltage	200	—	—	V	V_{GS} = 0V, I_D = 1.0mA
$\Delta BV_{DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	0.29	—	V/°C	Reference to 25°C, I_D = 1.0mA
$R_{DS(on)}$	Static Drain-to-Source On-State Resistance	—	—	0.18	Ω	V_{GS} = 10V, I_{D2} = 11A [1]
		—	—	0.25		V_{GS} = 10V, I_{D2} = 18A [1]
$V_{GS(th)}$	Gate Threshold Voltage	2.0	—	4.0	V	V_{DS} = V_{GS}, I_D = 250µA
Gfs	Forward Transconductance	6.1	—	—	S	V_{DS} = 15V, I_{D2} = 11A [1]
I_{DSS}	Zero Gate Voltage Drain Current	—	—	25	µA	V_{DS} = 160V, V_{GS} = 0V
		—	—	250		V_{DS} = 160V,V_{GS} = 0V,T_J = 125°C
I_{GSS}	Gate-to-Source Leakage Forward	—	—	100	nA	V_{GS} = 20V
	Gate-to-Source Leakage Reverse	—	—	-100		V_{GS} = -20V
Q_G	Total Gate Charge	—	—	60	nC	I_{D1} = 18A V_{DS} = 100V V_{GS} = 10V
Q_{GS}	Gate-to-Source Charge	—	—	14.6		
Q_{GD}	Gate-to-Drain ('Miller') Charge	—	—	37.6		
$t_{d(on)}$	Turn-On Delay Time	—	—	20	ns	I_{D1} = 18A ** V_{DD} = 100V R_G = 9.1Ω V_{GS} = 10V
t_r	Rise Time	—	—	105		
$t_{d(off)}$	Turn-Off Delay Time	—	—	58		
t_f	Fall Time	—	—	67		
L_s +L_D	Total Inductance	—	4.0	—	nH	Measured from Drain lead (6mm / 0.25 in from package) to Source lead (6mm/ 0.25 in from package) with Source wire internally bonded from Source pin to Drain pad
C_{iss}	Input Capacitance	—	1300	—	pF	V_{GS} = 0V V_{DS} = 25V f = 1.0MHz
C_{oss}	Output Capacitance	—	400	—		
C_{rss}	Reverse Transfer Capacitance	—	130	—		

** Switching speed maximum limits are based on manufacturing test equipment and capability.

[1] Pulse width ≤ 300 µs; Duty Cycle ≤ 2%

2.2 Source-Drain Diode Ratings and Characteristics (Pre-Irradiation)

Table 4 Source-Drain Diode Characteristics

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions
I_S	Continuous Source Current (Body Diode)	—	—	18	A	
I_{SM}	Pulsed Source Current (Body Diode) [1]	—	—	72	A	
V_{SD}	Diode Forward Voltage	—	—	1.5	V	T_J = 25°C, I_S = 18A, V_{GS} = 0V [2]
t_{rr}	Reverse Recovery Time	—	—	500	ns	T_J = 25°C, I_F = 18A, V_{DD} ≤ 50V di/dt = 100A/µs [2]
Q_{rr}	Reverse Recovery Charge	—	—	5.3	µC	
t_{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by L_S+L_D)				

2.3 Thermal Characteristics

Table 5 Thermal Resistance

Symbol	Parameter	Min.	Typ.	Max.	Unit
$R_{\theta JC}$	Junction-to-Case	—	—	1.0	°C/W
$R_{\theta CS}$	Case-to-Sink	—	0.21	—	
$R_{\theta JA}$	Junction-to-Ambient (Typical socket mount)	—	—	48	

[1] Repetitive Rating; Pulse width limited by maximum junction temperature.
[2] Pulse width ≤ 300 µs; Duty Cycle ≤ 2%

3 Electrical Characteristics Curves (Pre-irradiation)

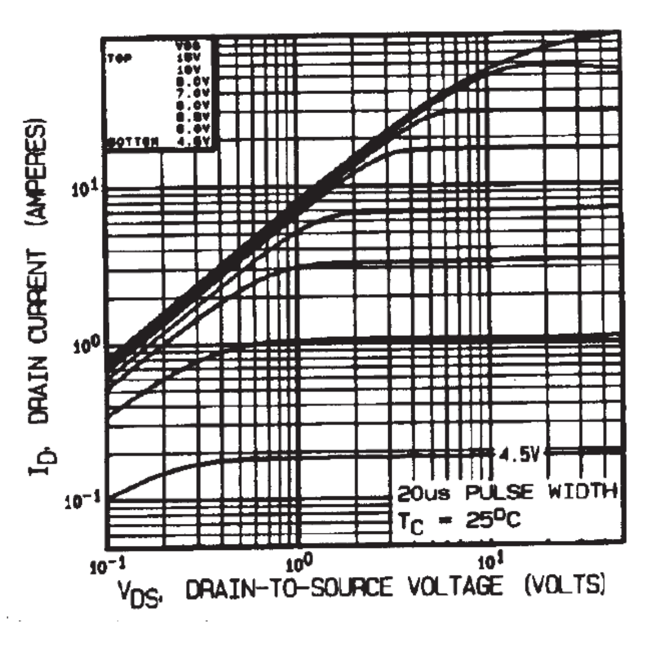


Figure 1 Typical Output Characteristics

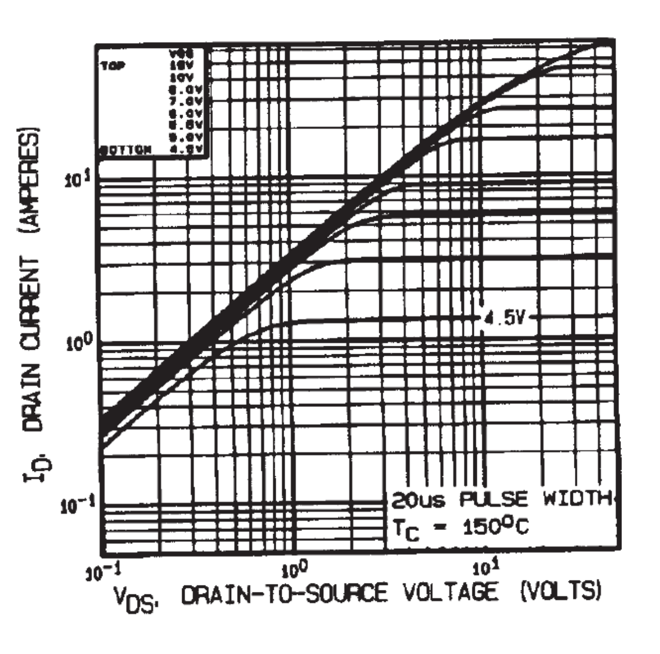


Figure 2 Typical Output Characteristics

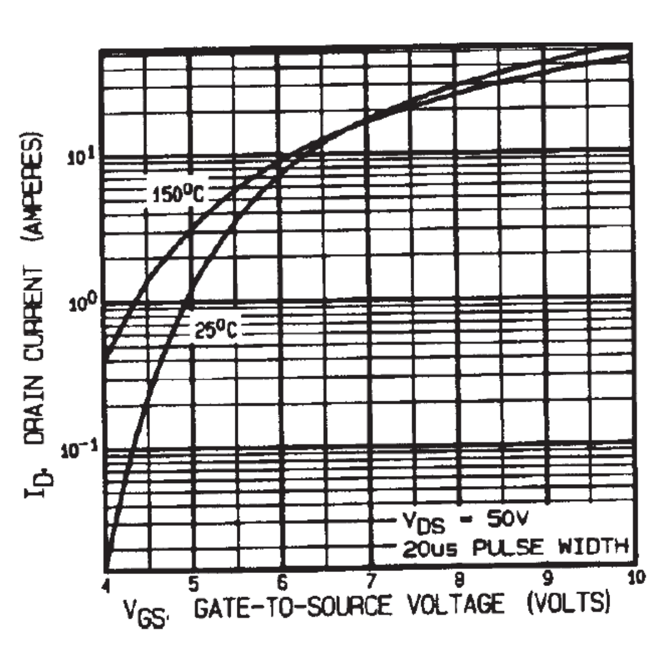


Figure 3 Typical Transfer Characteristics

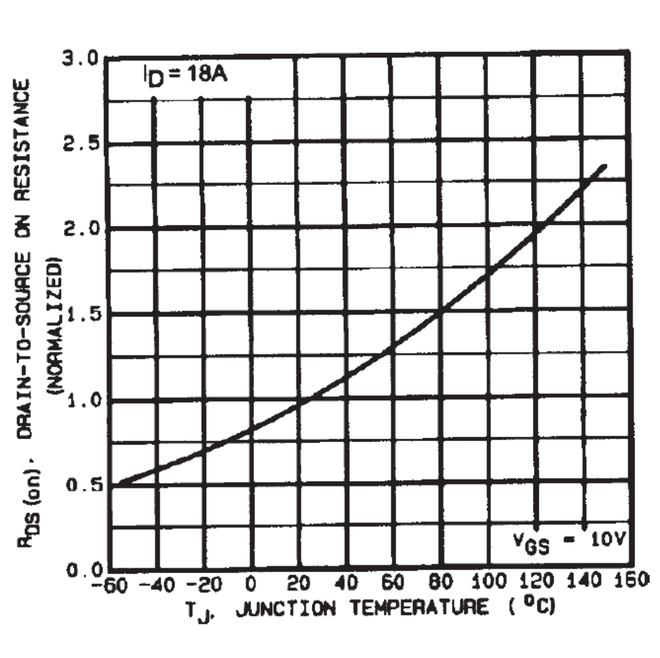


Figure 4 Normalized On-Resistance Vs. Temperature

Electrical Characteristics Curves (Pre-irradiation)

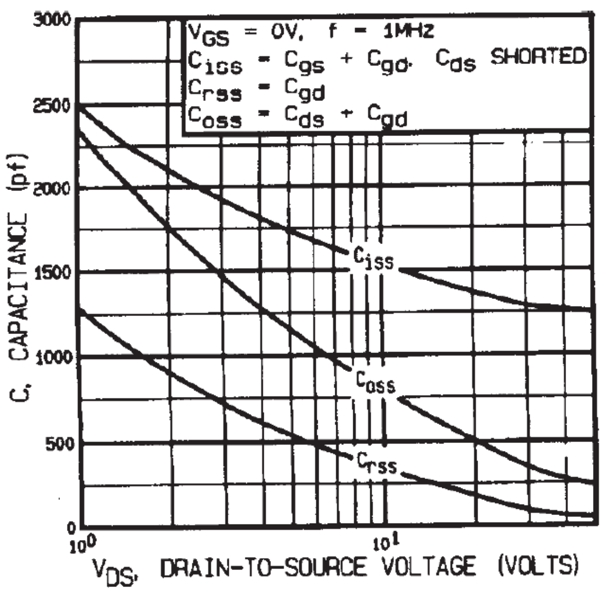


Figure 5 **Typical Capacitance Vs. Drain-to-Source Voltage**

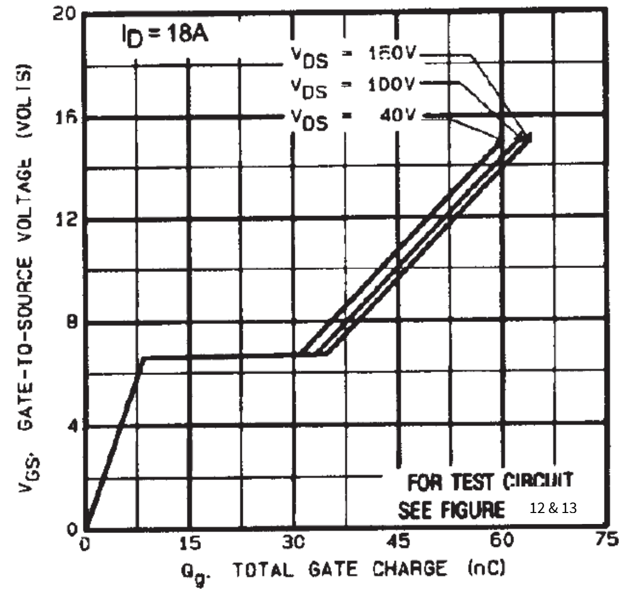


Figure 6 **Typical Gate Charge Vs. Gate-to-Source Voltage**

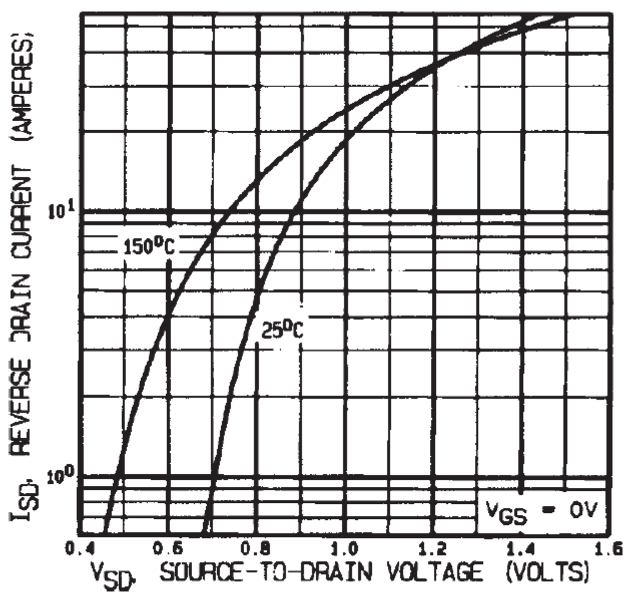


Figure 7 **Typical Source-Drain Current Vs. Diode Forward Voltage**

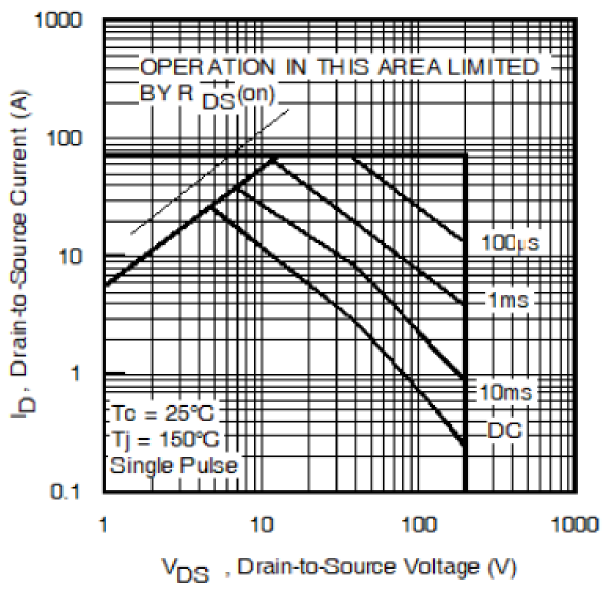


Figure 8 **Maximum Safe Operating Area**

Electrical Characteristics Curves (Pre-irradiation)

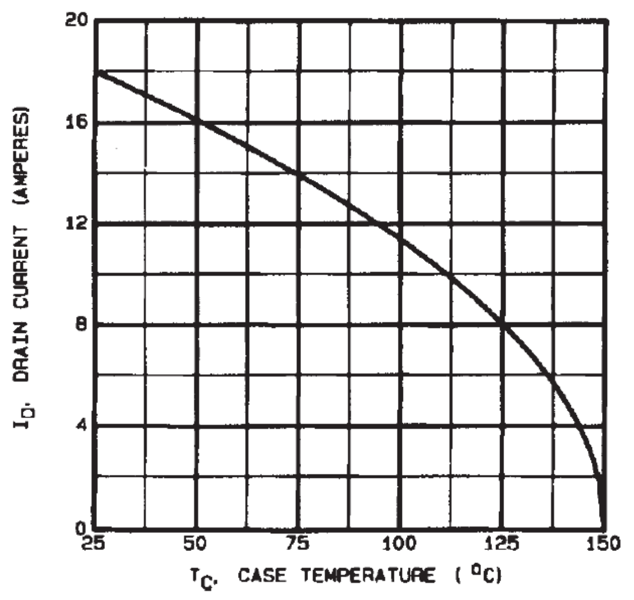


Figure 9 Maximum Drain Current Vs. Case Temperature

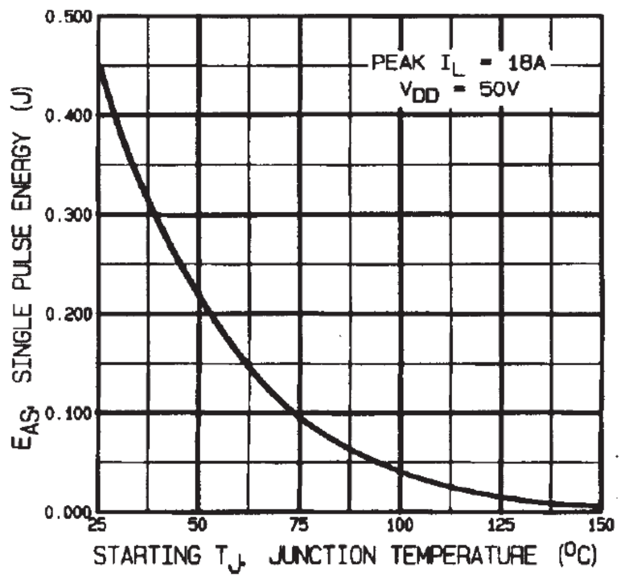


Figure 10 Maximum Avalanche Energy Vs. Junction Temperature

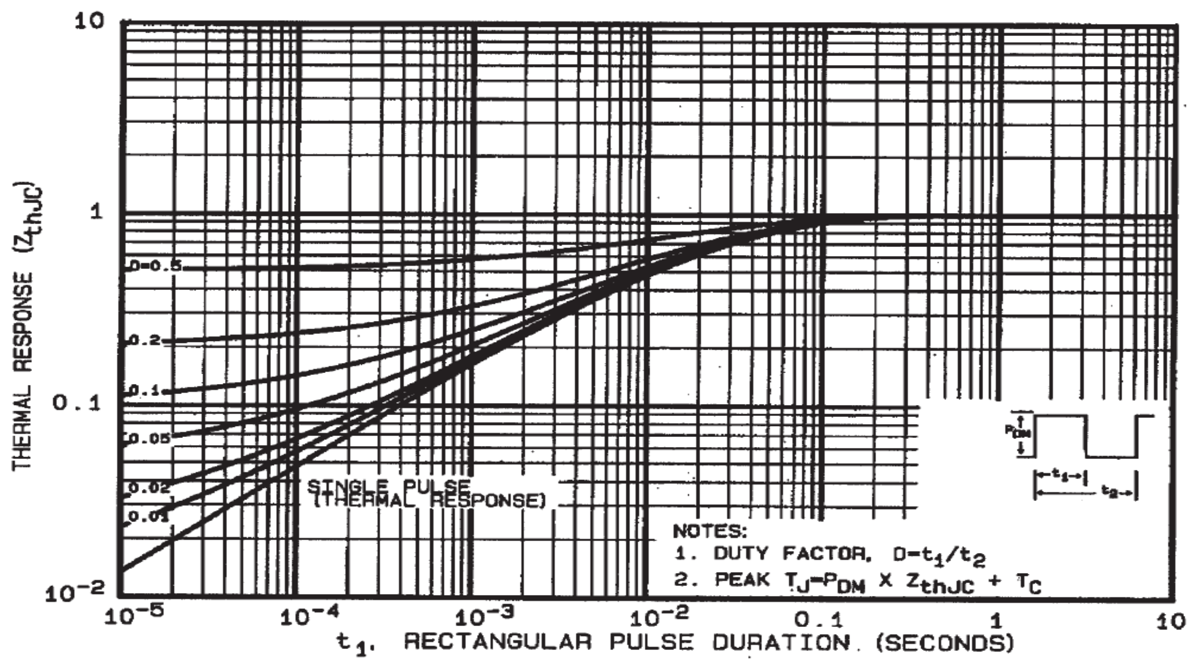


Figure 11 Maximum Effective Transient Thermal Impedance, Junction-to-Case

4 Test Circuits (Pre-irradiation)

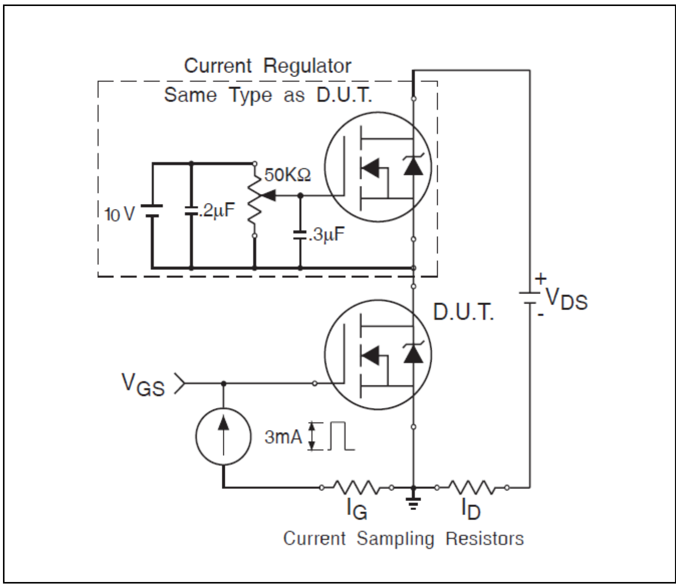


Figure 12 Gate Charge Test Circuit

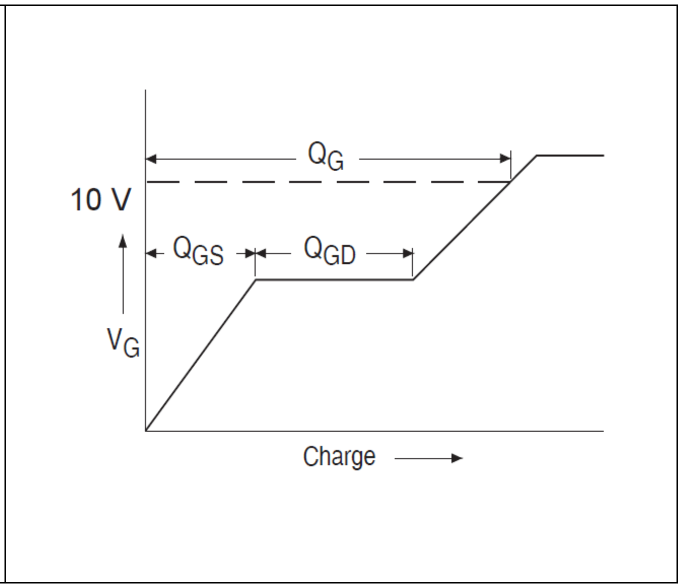


Figure 13 Gate Charge Waveform

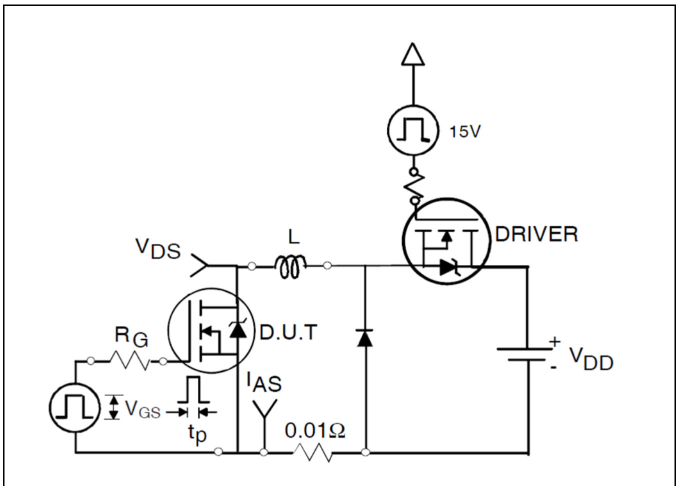


Figure 14 Unclamped Inductive Test Circuit

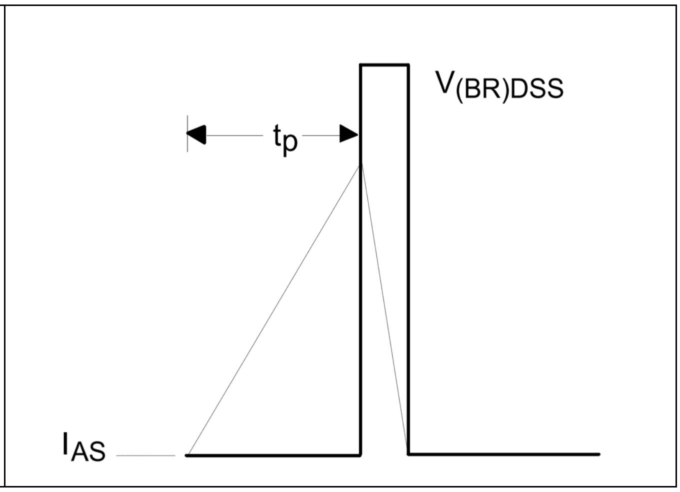


Figure 15 Unclamped Inductive Waveform

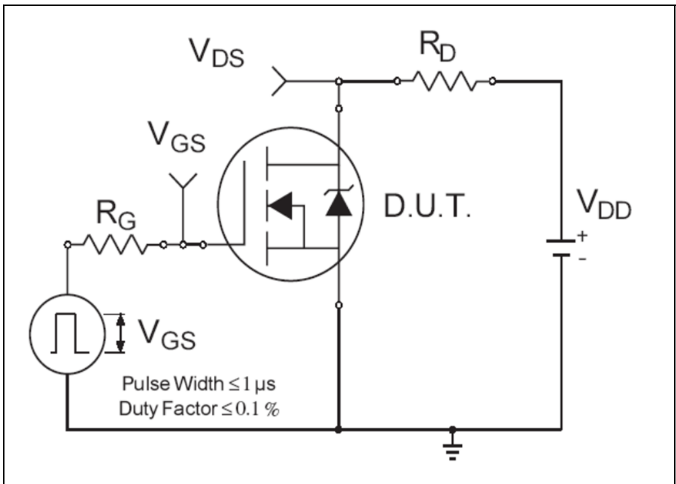


Figure 16 Switching Time Test Circuit

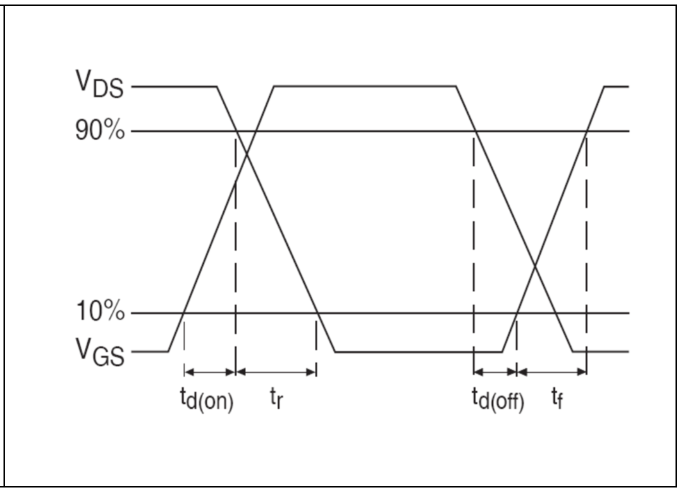
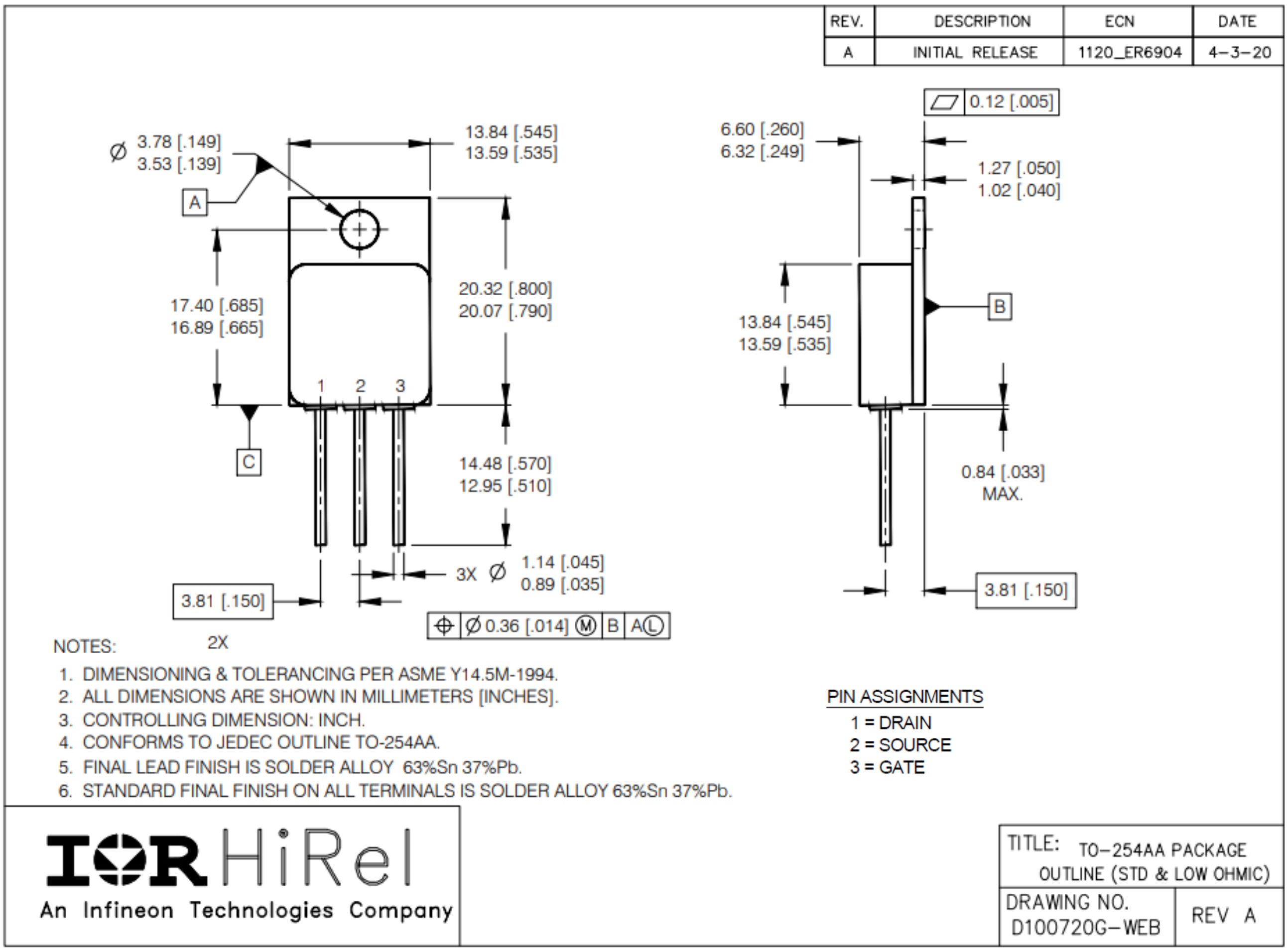


Figure 17 Switching Time Waveforms

5 Package Outline

Note: For the most updated package outline, please see the website: TO-254AA



BERYLLIA WARNING PER MIL-PRF-19500

Package containing beryllia shall not be ground, sandblasted, machined, or have other operations performed on them which will produce beryllia or beryllium dust. Furthermore, beryllium oxide packages shall not be placed in acids that will produce fumes containing beryllium.

Revision history

Document version	Date of release	Description of changes
Rev D	01/29/2002	Datasheet (PD-90555D)
Rev E	04/20/2007	Updated based on ECN-14806
Rev F	12/09/2021	Updated based on ECN-1120_08867

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